

IGBT XPT Module

H Bridge

$$V_{CES} = 1200 \text{ V}$$

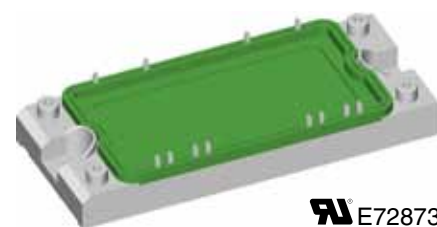
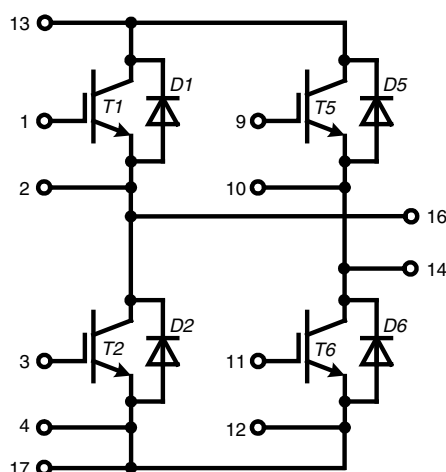
$$I_{C25} = 85 \text{ A}$$

$$V_{CE(sat)} = 1.8 \text{ V}$$

Preliminary data

Part name (Marking on product)

MIXA 61H1200ED



E72873

Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - square RBSOA @ 3x I_C
 - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E2-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting

Output Inverter T1 - T6

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			85	A	
I_{C80}		$T_C = 80^{\circ}\text{C}$			60	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			290	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 55\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.8 2.1	2.1	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 2\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.4	6.0	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.5	mA mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 50\text{ A}$		165		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70		ns	
t_r	current rise time			40		ns	
$t_{d(off)}$	turn-off delay time			250		ns	
t_f	current fall time			100		ns	
E_{on}	turn-on energy per pulse			4.5		mJ	
E_{off}	turn-off energy per pulse			5.5		mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		150	A	
SCSOA	short circuit safe operating area						
t_{sc}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10	μs	
I_{sc}	short circuit current	$R_G = 15\text{ }\Omega;$ non-repetitive		200		A	
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.43	K/W	

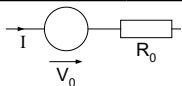
Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	<i>max. repetitive reverse voltage</i>		$T_{VJ} = 25^{\circ}\text{C}$		1200	V
I_{F25}	<i>forward current</i>		$T_C = 25^{\circ}\text{C}$		85	A
I_{F80}			$T_C = 80^{\circ}\text{C}$		57	A
V_F	<i>forward voltage</i>	$I_F = 60\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.95	2.2	V V
Q_{rr}	<i>reverse recovery charge</i>	$V_R = 600\text{ V}$ $di_F/dt = -1200\text{ A}/\mu\text{s}$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	8		μC
I_{RM}	<i>max. reverse recovery current</i>			60		A
t_{rr}	<i>reverse recovery time</i>			350		ns
E_{rec}	<i>reverse recovery energy</i>			2.5		mJ
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			0.6	K/W

$T_C = 25^{\circ}\text{C}$ unless otherwise stated

Module

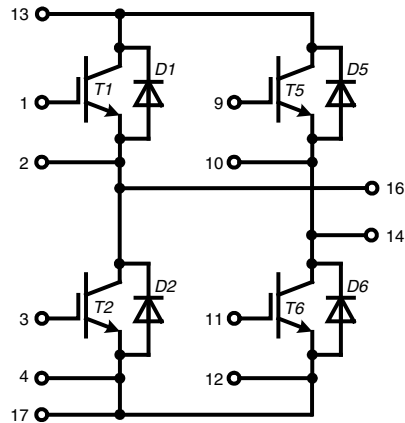
Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			3000	V~
CTI	comparative tracking index				-	
M_d	mounting torque (M5)		3		6	Nm
d_s	creep distance on surface		6			mm
d_A	strike distance through air		6			mm
$R_{pin-chip}$	resistance pin to chip			5		mΩ
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				180		g

Equivalent Circuits for Simulation


Symbol	Definitions	Conditions	min.	Ratings		Unit
				typ.	max.	
V_0	IGBT	T1 - T6	$T_{VJ} = 150^\circ\text{C}$	1.1		V
R_0				25.1		mΩ
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 150^\circ\text{C}$	1.22		V
R_0				12.99		mΩ

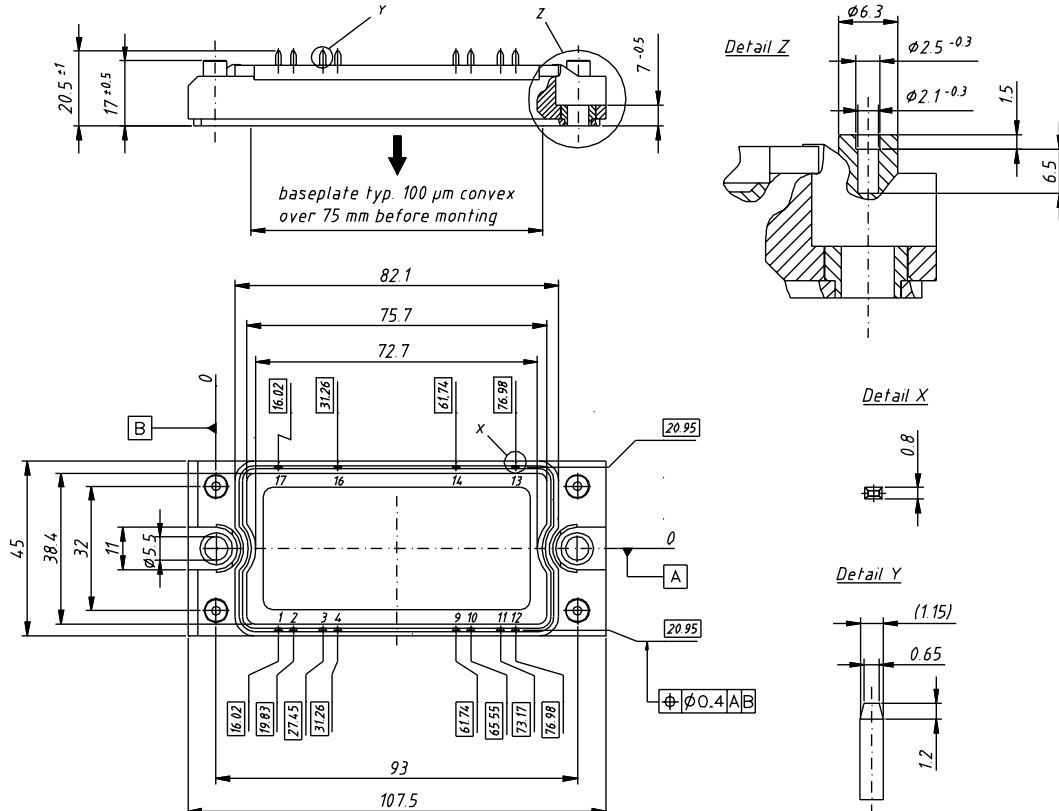
$T_C = 25^\circ\text{C}$ unless otherwise stated

Circuit Diagram

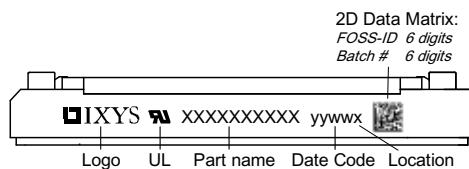


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking



Part number

M = Module
I = IGBT
X = XPT
A = standard
61 = Current Rating [A]
H = H~ Bridge
1200 = Reverse Voltage [V]
ED = E2-Pack

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA61H1200ED	MIXA61H1200ED	Box	6	511060

IXYS reserves the right to change limits, test conditions and dimensions.

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Inverter T1 - T6

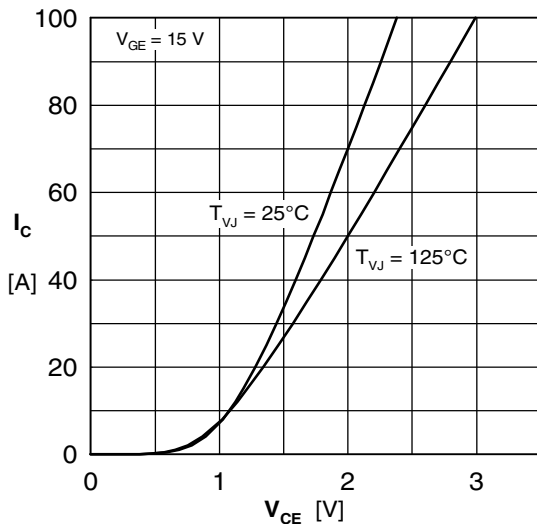


Fig. 1 Typ. output characteristics

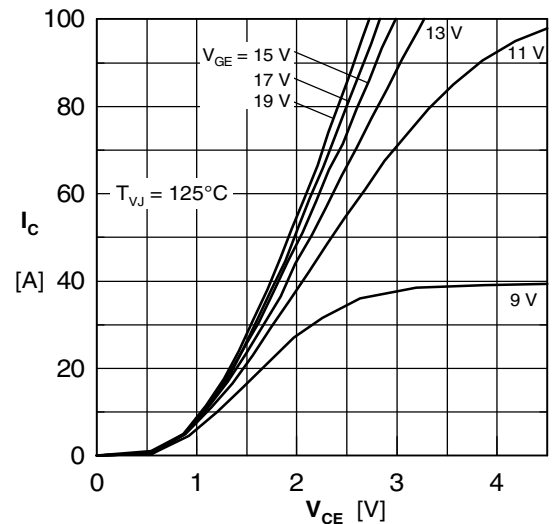


Fig. 2 Typ. output characteristics

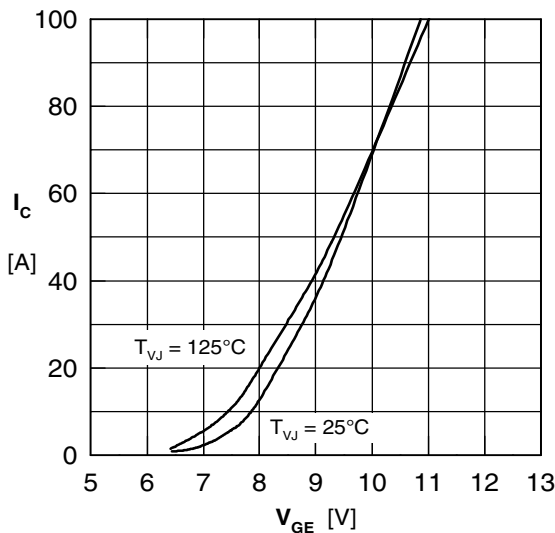


Fig. 3 Typ. transfer characteristics

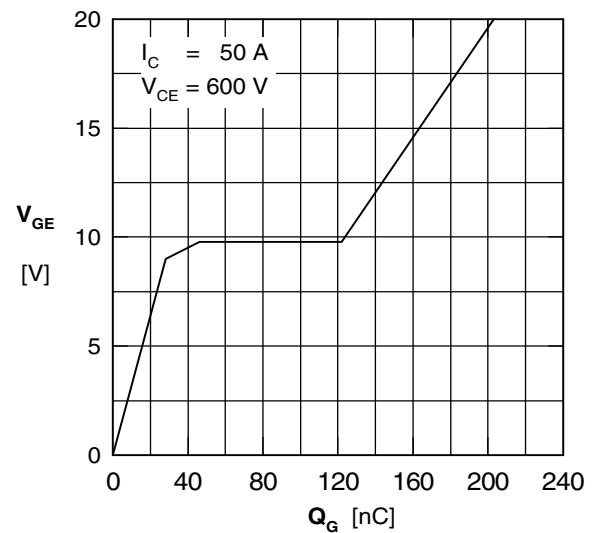


Fig. 4 Typ. turn-on gate charge

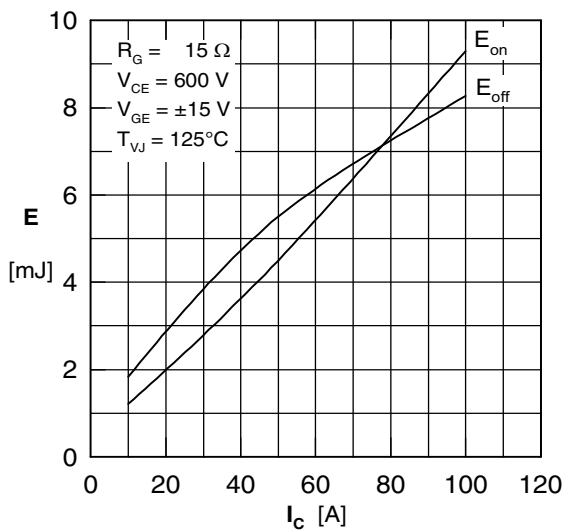


Fig. 5 Typ. switching energy vs. collector current

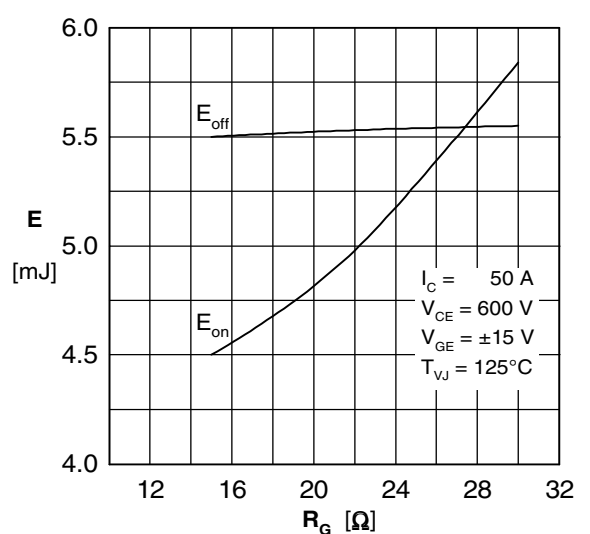


Fig. 6 Typ. switching energy vs. gate resistance

Inverter D1 - D6

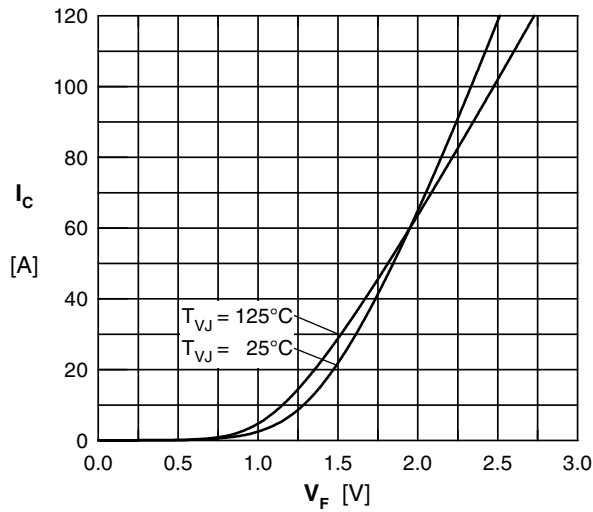


Fig. 7 Typ. Forward current versus V_F

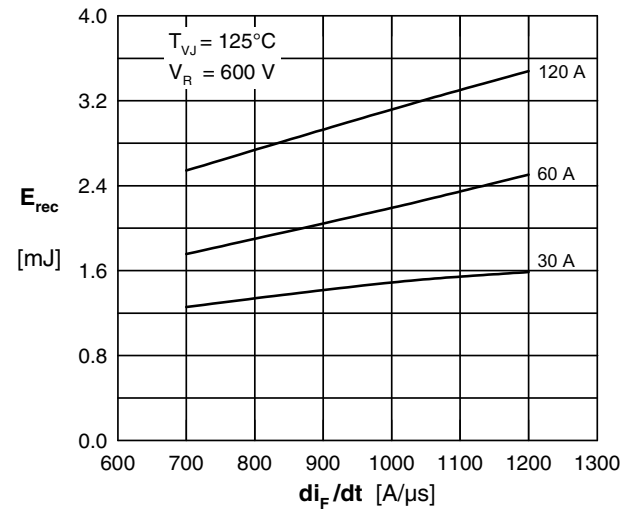


Fig. 8 Typ. recovery energy E_{rec} versus di/dt

	IGBT		FRD	
	R_i	τ_i	R_i	τ_i
1	0.1	0.0025	0.137	0.0025
2	0.05	0.03	0.1	0.03
3	0.21	0.03	0.233	0.03
4	0.07	0.08	0.13	0.08

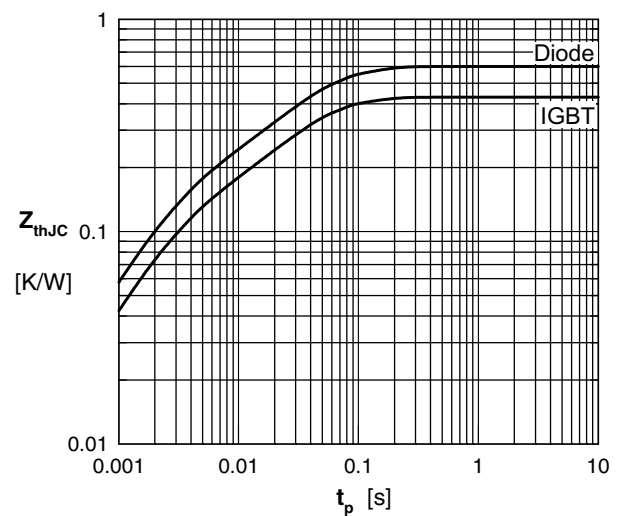


Fig. 9 Typ. transient thermal impedance